

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE		Atty. Docket No. YOR920030334US1 (16899)	Serial No. 10/786,901
<b>LIST OF REFERENCES CITED BY APPLICANT</b> (Use several sheets if necessary)		Applicant: Ricky S. Amos et al.	
		Filing Date: February 25, 2004	Group/Art Unit: 2891

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (if appropriate)
AKS	4,780,429	10/25/1988	Roche et al.			
	5,986,313	11/16/1999	Ueda et al.			
	6,458,702	10/1/2002	Aloni			
	6,656,764	12/2/2003	Wang et al.			
	2002/123222	9/5/2002	Wu			
AKS	2003/230811	12/18/2003	Kim			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
AKS	2 804 793	8/10/2001	France				
	WO 99/53535	10/21/1999	PCT				
AKS	2002-217411	8/2/2002	Japan				

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

AKS	"Self-Aligned Technique Employing Planarized Resist For Reducing Poly-Silicon Sheet Resistance By Formation of a Metal Silicide." IBM Technical Disclosure Bulletin, IBM Corp. Vol. 30 No. 5 (1987)

EXAMINER: <i>Ashe Kumar Sathar</i>	DATE CONSIDERED: <i>11/30/06</i>
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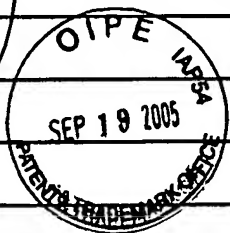
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**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

Docket Number (Optional) <b>YOR920030334US1 (16899)</b>		Application Number <b>10/786,901</b>
Applicant(s) <b>Ricky S. Amos et al.</b>		
Filing Date <b>February 25, 2004</b>		Group Art Unit <b>2891</b>

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE



**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AKS		2003/0141565 A1	7/31/2003	Hirose et al.			

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

AKS		Oh J. et al. "Interdigitated Ge p-i-n Photodetectors Fabricated on a Si Substrate Using Graded SiGe Buffer Layers." IEEE Journal of Quantum Electronics, vol. 38, no. 9, (2002)
AKS		Jones R.E. et al. "Fabrication and Modeling of Gigahertz Photodetectors in Heteroepitaxial Ge-on-Si Using a Graded Buffer Layer Deposited by Low Energy Plasma Enhanced CVD." IEDM p793 (2002)

EXAMINER <b>Asst. Examiner Sarah</b>	DATE CONSIDERED <b>1/30/06</b>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.